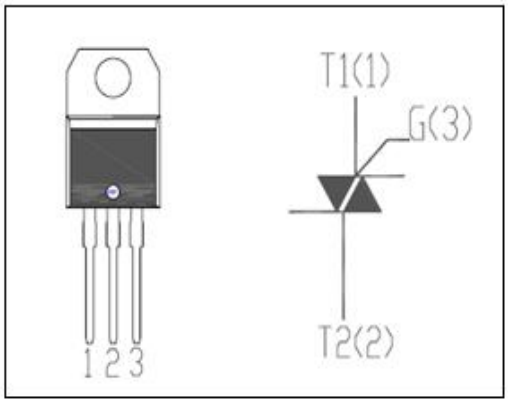
isc Thyristors BTA16-800BRG

DESCRIPTION

- With TO-220 insulated packaging
- Operating in 4 quadrants
- High commutation capability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Switching applications
- Phase control
- Static switching on inductive or resistive load

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER		Max	UNIT
V_{DRM}	Repetitive peak off-state voltage		800	V
V_{RRM}	Repetitive peak reverse voltage		800	V
$I_{T(RSM)}$	Average on-state current Tc=15℃		16	A
I_{TSM}	Surge non-repetitive on-state current	50HZ 60HZ	160 168	A
$P_{G(AV)}$	Average gate power dissipation (over any 20 ms period) Tj=125℃		1	W
T_j	Operating junction temperature		-40~125	℃
T_{stg}	Storage temperature		-40~150	℃

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ELECTRICAL CHARACTERISTICS (T_C=25℃ unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS		MIN	MAX	UNIT
I_{RRM}	Repetitive peak reverse current	V_R=V_{RRM} Rated; V_D=V_{DRM} Rated;	Tj=25℃		5	μA
I_{DRM}	Repetitive peak off-state current		Tj=125℃		2	mA
V_{TM}	On-state voltage	I_T=22.5A； t_P=380μs			1.55	V
I_{GT}	Gate-trigger current	V_D =12V;R_L=33Ω;	Ⅰ		50	mA
			Ⅱ		50	
			Ⅲ		50	
			Ⅳ		100	
V_{GT}	Gate-trigger voltage	V_D =12V;R_L=33Ω;			1.3	V
Rth $_{(j-c)}$	Junction to case				2.1	℃/W